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(71) Applicant *(for all designated States except US)*: **ADVANCED MICRO DEVICES, INC.** [US/US]; One AMD Place Mail Stop 68, P.O. Box 3453, Sunnyvale, CA 94088-3453 (US).

(72) Inventors; and

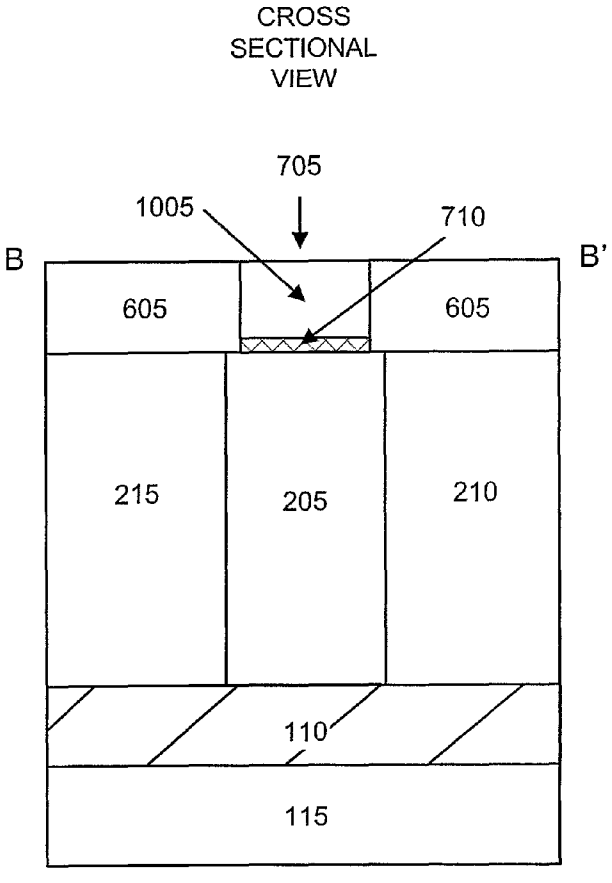
(75) Inventors/Applicants *(for US only)*: **AHMED, Shibly, S.** [BD/US]; 350 Elan Village Lane, #105, San Jose, CA 95134 (US). **WANG, Haihong** [CN/US]; 1775 Milmont Drive, Apt. T303, Milpitas, CA 95035 (US). **YU, Bin** [CN/US]; 1373 Poppy Way, Cupertino, CA 95014 (US).

(74) Agent: **DRAKE, Paul, S.**; One AMD Place, Mail Stop 68, P.O. Box 3453, Sunnyvale, CA 94088-3453 (US).

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(54) Title: NARROW-BODY DAMASCENE TRI-GATE FINFET HAVING THINNED BODY



(57) Abstract: A method of forming a fin field effect transistor includes forming a fin (205) and forming a source region (210) on a first end of the fin (205) and a drain region (215) on a second end of the fin (205). The method further includes forming a dummy gate (505) with a first semiconducting material in a first pattern over the fin (205) and forming a dielectric layer (605) around the dummy gate (505). The method also includes removing the first semiconducting material to leave a trench (705) in the dielectric layer (605) corresponding to the first pattern, thinning a portion of the fin (205) exposed within the trench (705), and forming a metal gate (1005) within the trench (705).

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